

Dual N-Channel 20-V (D-S) MOSFET

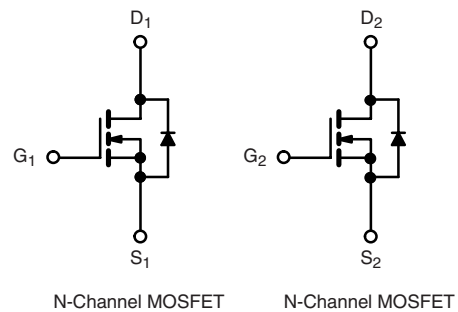
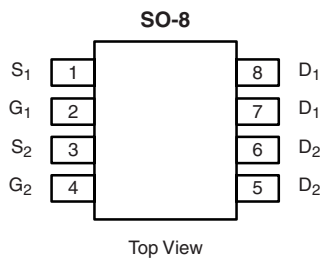
| PRODUCT SUMMARY | | |
|---------------------|----------------------------------|--------------------|
| V _{DS} (V) | R _{DS(on)} (Ω) | I _D (A) |
| 20 | 0.019 at V _{GS} = 4.5 V | 7.1 |
| | 0.026 at V _{GS} = 2.5 V | 6.0 |

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE
Available



| ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted | | | | |
|---|-----------------------------------|------------------------|------|--|
| Parameter | Symbol | Limit | Unit | |
| Drain-Source Voltage | V _{DS} | 20 | V | |
| Gate-Source Voltage | V _{GS} | ± 12 | | |
| Continuous Drain Current (T _J = 150 °C) ^a | I _D | T _A = 25 °C | A | |
| | | T _A = 70 °C | | |
| Pulsed Drain Current (10 μs Pulse Width) | I _{DM} | 40 | | |
| Continuous Source Current (Diode Conduction) ^a | I _S | 1.7 | | |
| Maximum Power Dissipation ^a | P _D | T _A = 25 °C | W | |
| | | T _A = 70 °C | | |
| Operating Junction and Storage Temperature Range | T _J , T _{stg} | - 55 to 150 | °C | |

| THERMAL RESISTANCE RATINGS | | | |
|--|-------------------|-------|------|
| Parameter | Symbol | Limit | Unit |
| Maximum Junction-to-Ambient ^a | R _{thJA} | 62.5 | °C/W |

Notes:

a. Surface Mounted on FR4 board, t ≤ 10 s.

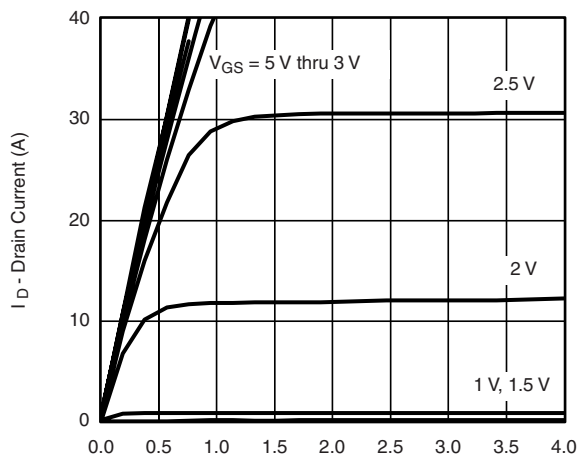
| SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted | | | | | | |
|---|--------------|---|------|-------|-----------|---------------|
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
| Static | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$ | 0.6 | | 1.5 | V |
| Gate-Body Leakage | I_{GSS} | $V_{DS} = 0\ \text{V}, V_{GS} = \pm 12\ \text{V}$ | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 20\ \text{V}, V_{GS} = 0\ \text{V}$ | | | 1 | μA |
| | | $V_{DS} = 20\ \text{V}, V_{GS} = 0\ \text{V}, T_J = 55\text{ }^\circ\text{C}$ | | | 5 | |
| On-State Drain Current ^a | $I_{D(on)}$ | $V_{DS} \geq 5\ \text{V}, V_{GS} = 4.5\ \text{V}$ | 20 | | | A |
| Drain-Source On-State Resistance ^a | $R_{DS(on)}$ | $V_{GS} = 4.5\ \text{V}, I_D = 7.1\ \text{A}$ | | 0.019 | | Ω |
| | | $V_{GS} = 2.5\ \text{V}, I_D = 6.0\ \text{A}$ | | 0.026 | | |
| Forward Transconductance ^a | g_{fs} | $V_{DS} = 10\ \text{V}, I_D = 7.1\ \text{A}$ | | 27 | | S |
| Diode Forward Voltage ^a | V_{SD} | $I_S = 1.7\ \text{A}, V_{GS} = 0\ \text{V}$ | | | 1.2 | V |
| Dynamic^b | | | | | | |
| Total Gate Charge | Q_g | $V_{DS} = 10\ \text{V}, V_{GS} = 4.5\ \text{V}, I_D = 7.1\ \text{A}$ | | 9.5 | | nC |
| Gate-Source Charge | Q_{gs} | | | 1.5 | | |
| Gate-Drain Charge | Q_{gd} | | | 2.5 | | |
| Gate Resistance | R_g | $f = 1\ \text{MHz}$ | | 1.6 | 2.7 | Ω |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = 10\ \text{V}, R_L = 10\ \Omega$ $I_D \cong 1\ \text{A}, V_{GEN} = 4.5\ \text{V}, R_g = 10\ \Omega$ | | 10 | | ns |
| Rise Time | t_r | | | 15 | | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 38 | | |
| Fall Time | t_f | | | 25 | | |
| Source-Drain Reverse Recovery Time | t_{rr} | $I_F = 1.7\ \text{A}, dI/dt = 100\ \text{A}/\mu\text{s}$ | | 26 | | |

Notes:

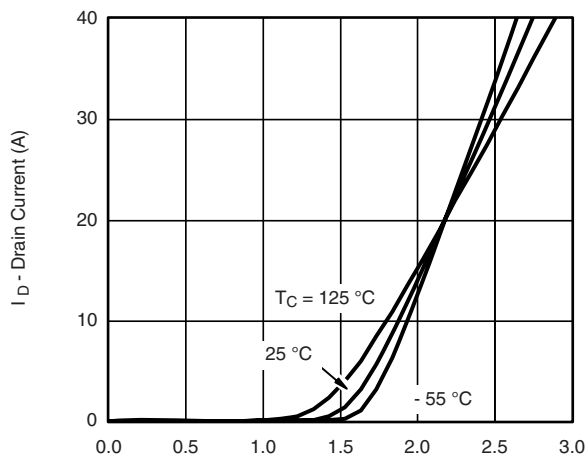
- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

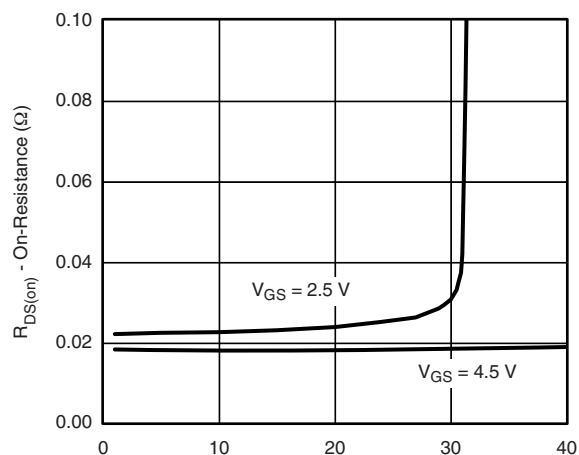
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



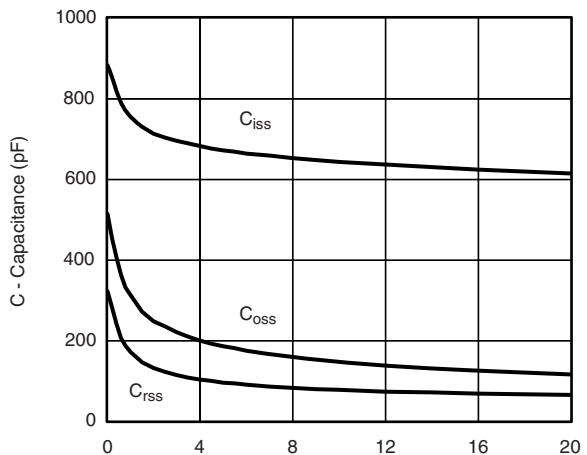
V_{DS} - Drain-to-Source Voltage (V)
Output Characteristics



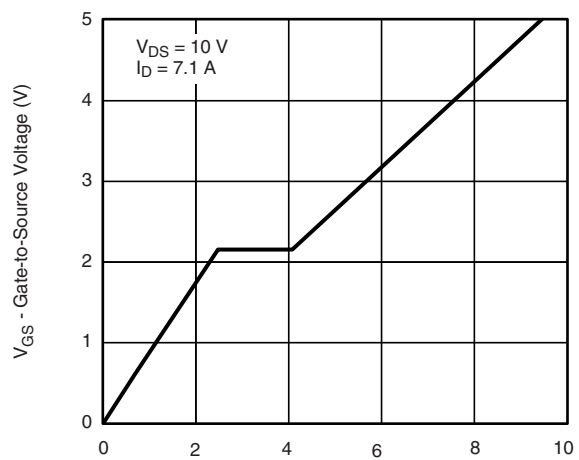
V_{GS} - Gate-to-Source Voltage (V)
Transfer Characteristics



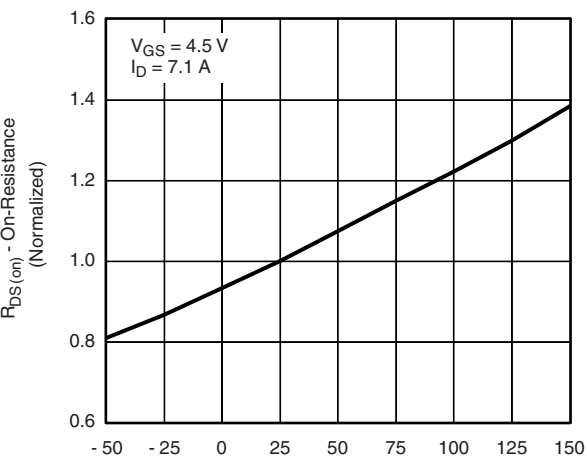
I_D - Drain Current (A)
On-Resistance vs. Drain Current



V_{DS} - Drain-to-Source Voltage (V)
Capacitance

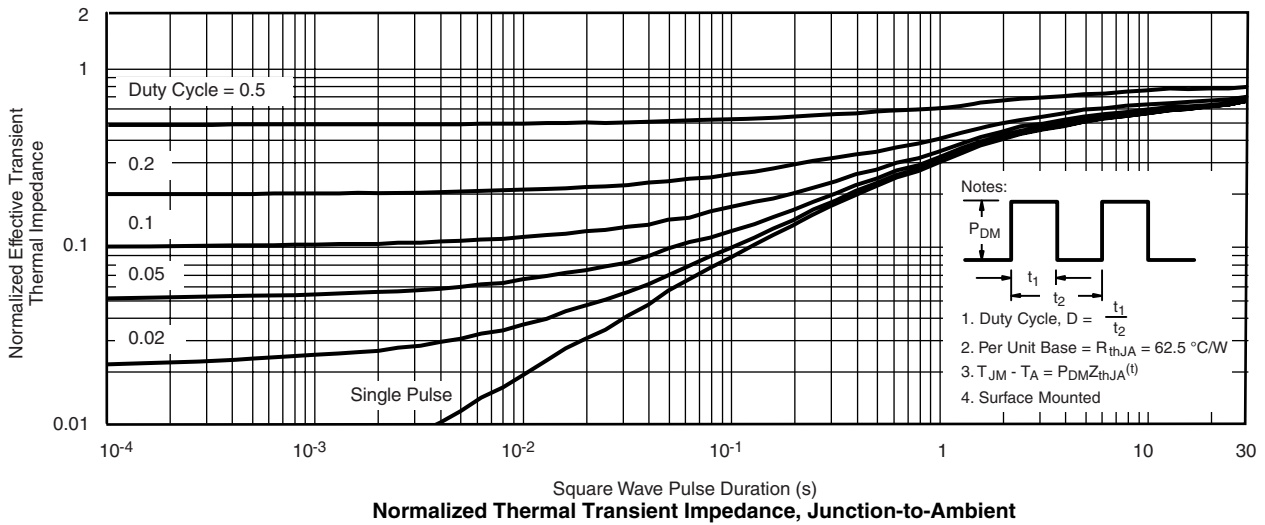
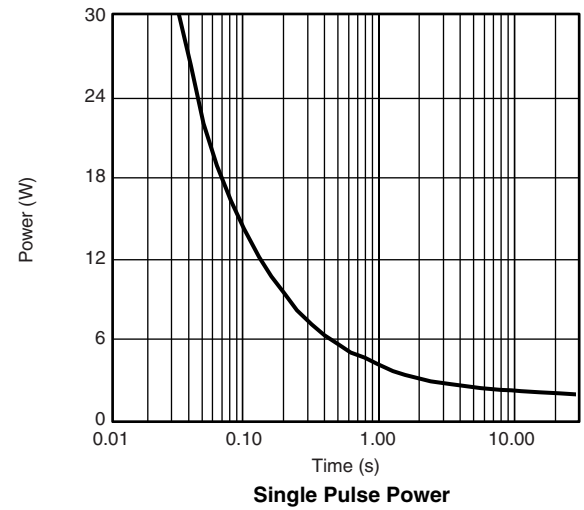
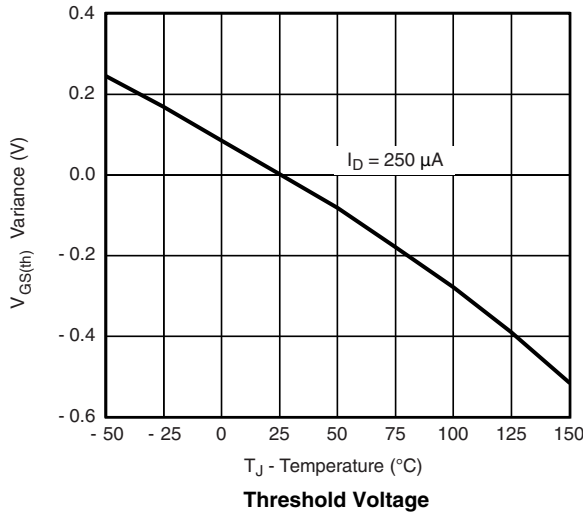
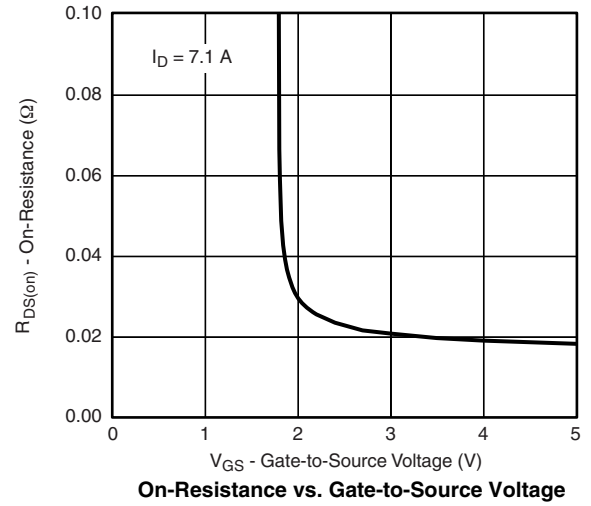
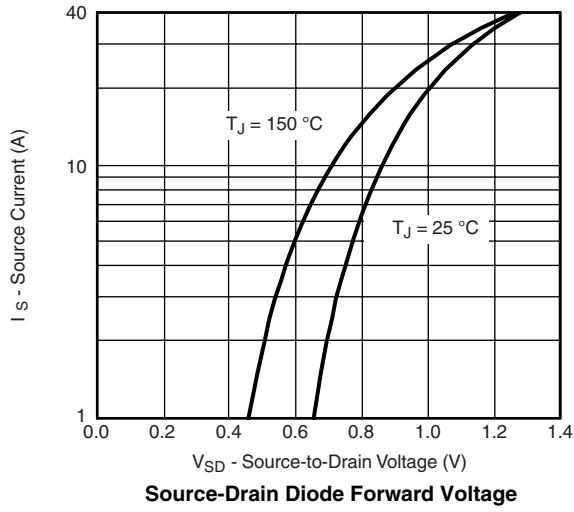


Q_g - Total Gate Charge (nC)
Gate Charge

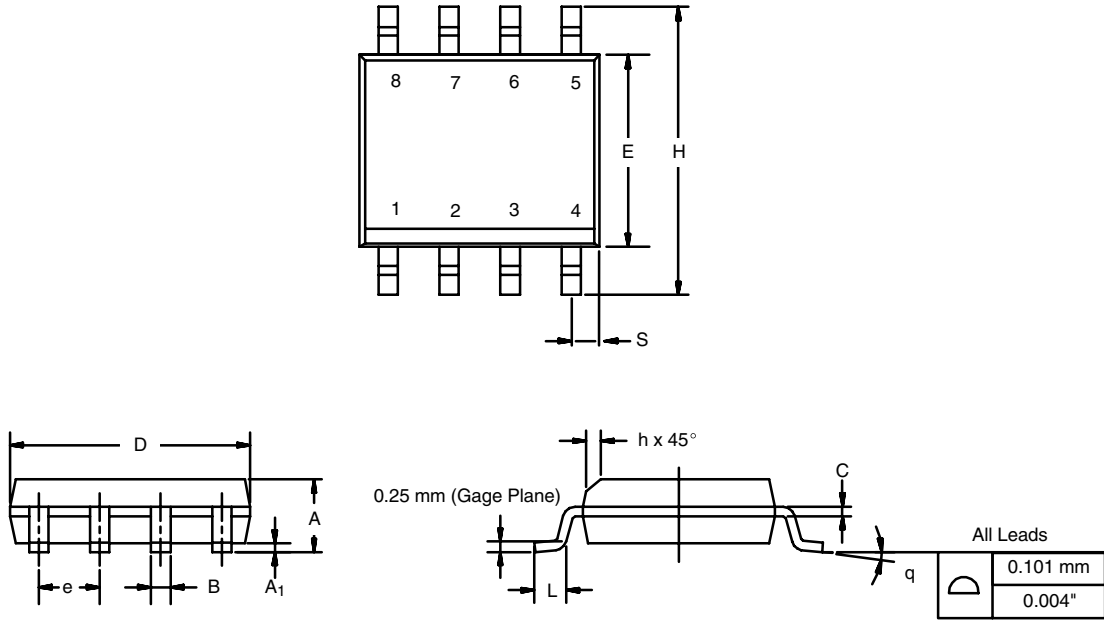


T_J - Junction Temperature ($^{\circ}\text{C}$)
On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

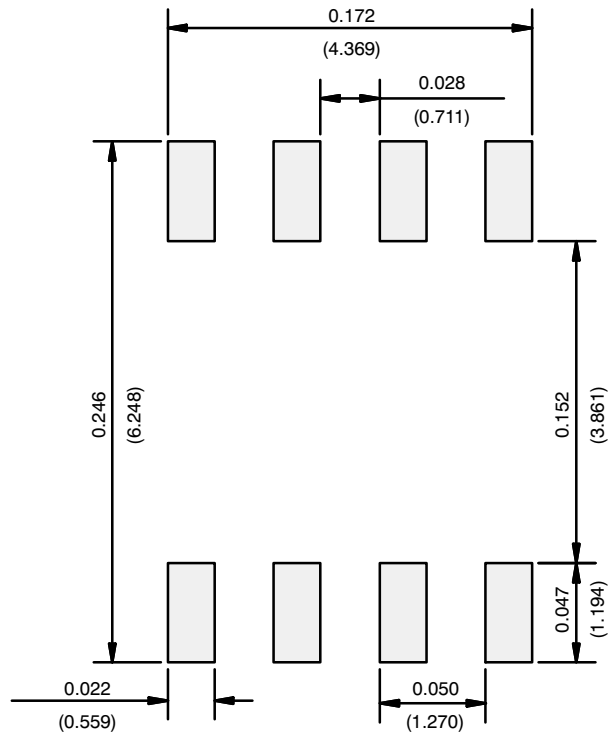


SOIC (NARROW): 8-LEAD
JEDEC Part Number: MS-012



| DIM | MILLIMETERS | | INCHES | |
|--------------------------------|-------------|------|-----------|-------|
| | Min | Max | Min | Max |
| A | 1.35 | 1.75 | 0.053 | 0.069 |
| A ₁ | 0.10 | 0.20 | 0.004 | 0.008 |
| B | 0.35 | 0.51 | 0.014 | 0.020 |
| C | 0.19 | 0.25 | 0.0075 | 0.010 |
| D | 4.80 | 5.00 | 0.189 | 0.196 |
| E | 3.80 | 4.00 | 0.150 | 0.157 |
| e | 1.27 BSC | | 0.050 BSC | |
| H | 5.80 | 6.20 | 0.228 | 0.244 |
| h | 0.25 | 0.50 | 0.010 | 0.020 |
| L | 0.50 | 0.93 | 0.020 | 0.037 |
| q | 0° | 8° | 0° | 8° |
| S | 0.44 | 0.64 | 0.018 | 0.026 |
| ECN: C-06527-Rev. I, 11-Sep-06 | | | | |
| DWG: 5498 | | | | |

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

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